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Vishay Semiconductors

# Hyperfast Rectifier, 8 A FRED Pt®



TO-220AC



TO-220 FULL-PAK





VS-8ETH06PbF VS-8ETH06-N3

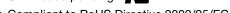
Cathode

VS-8ETH06FPPbF VS-8ETH06FP-N3

PRODUCT SUMMARY					
Package	TO-220AC, TO-220FP				
I <sub>F(AV)</sub>	8 A				
V <sub>R</sub>	600 V				
V <sub>F</sub> at I <sub>F</sub>	2.4 V				
t <sub>rr</sub> typ.	18 ns				
T <sub>J</sub> max.	175 °C				
Diode variation	Single die				

#### **FEATURES**

- · Hyperfast recovery time
- · Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Fully isolated package (V<sub>INS</sub> = 2500 V<sub>RMS</sub>)
- UL E78996 pending





- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified according to JEDEC-JESD47
- Halogen-free according to IEC 61249-2-21 definition (-N3 only)



FREE

#### **DESCRIPTION/APPLICATIONS**

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Repetitive peak reverse voltage	$V_{RRM}$		600	V			
Average restified forward current	,	T <sub>C</sub> = 144 °C	8				
Average rectified forward current FULL-Page 1	AK I <sub>F(AV)</sub>	T <sub>C</sub> = 108 °C					
Non repetitive pools over a comment	,	T <sub>J</sub> = 25 °C	90	А			
Non-repetitive peak surge current FULL-P	AK I <sub>FSM</sub>		100				
Repetitive peak forward current	I <sub>FM</sub>		16				
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		- 65 to 175	°C			

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	Ι <sub>R</sub> = 100 μΑ	600	-	-		
Forward voltage		I <sub>F</sub> = 8 A	-	2.0	2.4	V	
	$V_{F}$	I <sub>F</sub> = 8 A, T <sub>J</sub> = 150 °C	-	1.3	1.8		
Reverse leakage current	a lankaga ayuwant	$V_R = V_R$ rated	-	0.3	50		
	I <sub>R</sub>	T <sub>J</sub> = 150 °C, V <sub>R</sub> = V <sub>R</sub> rated	-	55	500	μΑ	
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 600 V	-	17	-	pF	
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nH	

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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>C</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1 A, dI_F/dt = 100$	$I_F = 1 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		18	22		
Reverse recovery time	+	$I_F = 8 \text{ A}, dI_F/dt = 100$	V = 30 V	-	20	25	no	
neverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	25	-	ns - A	
		T <sub>J</sub> = 125 °C	$I_F = 8 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 390 \text{ V}$	-	40	-		
Dools recovery average	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C		-	2.4	-		
Peak recovery current		T <sub>J</sub> = 125 °C		-	4.8	-		
Daviawa wasawan ahawa	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	25	-	nC	
Reverse recovery charge		T <sub>J</sub> = 125 °C		-	120	-	nc nc	
Reverse recovery time	t <sub>rr</sub>		I <sub>F</sub> = 8 A	-	33	-	ns	
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	= 125 °C	-	12	-	Α	
Reverse recovery charge	Q <sub>rr</sub>		V <sub>R</sub> = 390 V	-	220	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 65	-	175	°C		
Thermal resistance,	$R_{thJC}$		1	1.4	2			
junction to case (FULL-PAK)	TthJC		-	3.4	4.3			
Thermal resistance, junction to ambient per leg	R <sub>thJA</sub>	Typical socket mount	-	-	70	°C/W		
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.5	-			
Maint			-	2.0	-	g		
Weight			-	0.07	-	OZ.		
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)		
Mayling daving		Case style TO-220AC	8ETH06		•			
Marking device		Case style TO-220 FULL-PAK		8ETH	106FP			

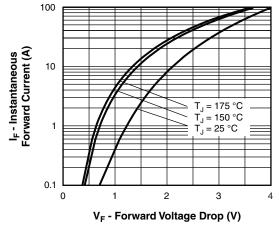


Fig. 1 - Typical Forward Voltage Drop Characteristics

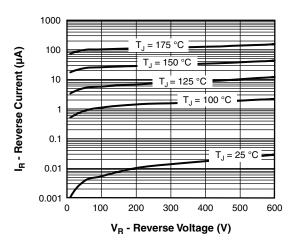


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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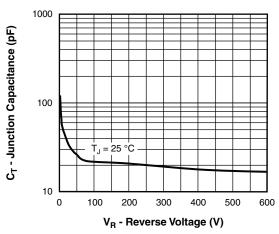


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

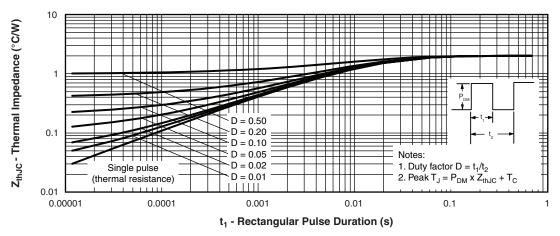


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

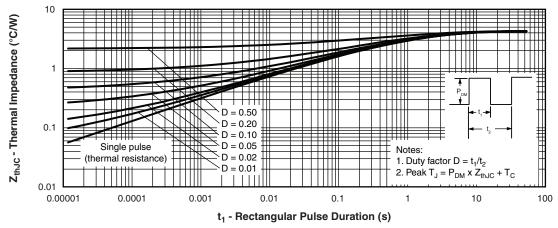


Fig. 5 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics (FULL-PAK)



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10

RMS limit

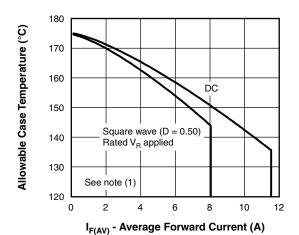
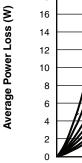
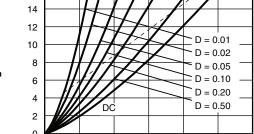


Fig. 6 - Maximum Allowable Case Temperature vs.



20

18



I<sub>F(AV)</sub> - Average Forward Current (A)

Fig. 8 - Forward Power Loss Characteristics

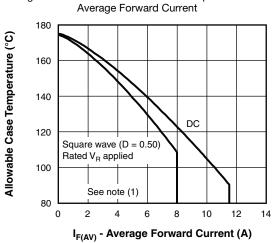


Fig. 7 - Maximum Allowable Case Temperature vs. Average Forward Current (FULL-PAK)

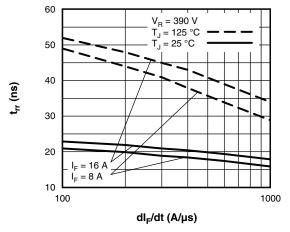


Fig. 9 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

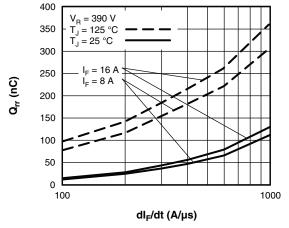


Fig. 10 - Typical Stored Charge vs. dI<sub>F</sub>/dt

#### Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 8)}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 8)}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 8)}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 8)}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 8)}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 8)}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 8)}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 8)}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 8)}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 8)}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 8)}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 8)}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 8)}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 8)}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ (see fig. 8)}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ (see fig. 8)}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ (see fig. 8)}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ (see fig. 8)}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ (see fig. 8)}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ (see fig. 8)}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ (see fig. 8)}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ (see fig. 8)}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ (see fig. 8)}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ (see fig. 8)}; \\ Pd = \text{Forward power loss} =$  $Pd_{REV}$  = Inverse power loss =  $V_{R1} \times I_{R} (1 - D)$ ;  $I_{R}$  at  $V_{R1}$  = Rated  $V_{R1}$ 

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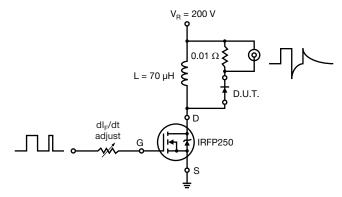
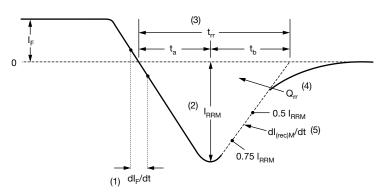


Fig. 11 - Reverse Recovery Parameter Test Circuit



- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_F$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{\rm rr}$  area under curve defined by  $\mathbf{t}_{\rm rr}$  and  $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

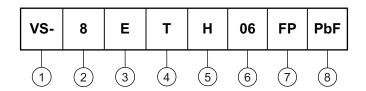
(5) dl<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 12 - Reverse Recovery Waveform and Definitions

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#### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

- Current rating (8 = 8 A)

3 - E = Single diode

T = TO-220, D<sup>2</sup>PAK

5 - H = Hyperfast recovery

6 - Voltage rating (06 = 600 V)

7 - • None = TO-220AC

• FP = TO-220 FULL-PAK

8 - Environmental digit:

PbF = Lead (Pb)-free and RoHS compliant

-N3 = Halogen-free, RoHS compliant and totally lead (Pb)-free

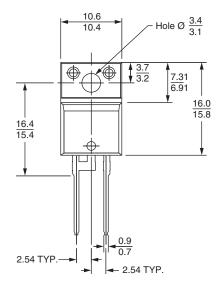
ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-8ETH06PbF	50	1000	Antistatic plastic tube				
VS-8ETH06-N3	50	1000	Antistatic plastic tube				
VS-8ETH06FPPbF	50	1000	Antistatic plastic tube				
VS-8ETH06FP-N3	50	1000	Antistatic plastic tube				

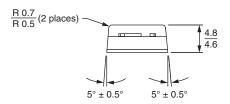
LINKS TO RELATED DOCUMENTS					
Dimensions	TO-220AC	www.vishay.com/doc?95221			
Differisions	TO-220FP	www.vishay.com/doc?95005			
Part marking information	TO-220ACPbF	www.vishay.com/doc?95224			
	TO-220AC-N3	www.vishay.com/doc?95068			
	TO-220FPPbF	www.vishay.com/doc?95009			
	TO-220FP-N3	www.vishay.com/doc?95440			

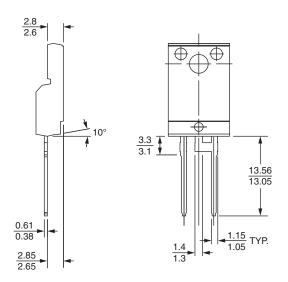


## Vishay Semiconductors

#### **DIMENSIONS** in millimeters







#### Lead assignments

<u>Diodes</u> 1 + 2 - Cathode 3 - Anode

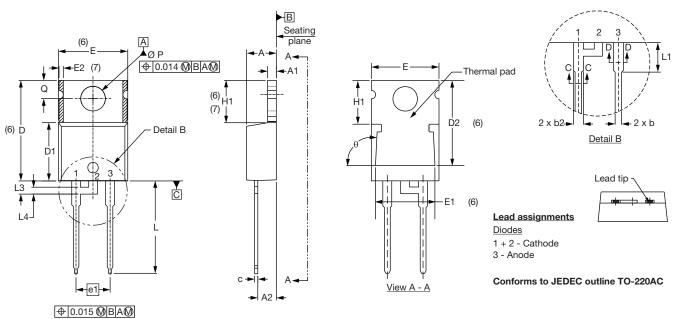
Conforms to JEDEC outline TO-220 FULL-PAK



### Vishay Semiconductors

### **TO-220AC**

#### **DIMENSIONS** in millimeters and inches



0)/14001	MILLIM	IETERS	INCHES		
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6
E	10.11	10.51	0.398	0.414	3, 6

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
L3	1.78	2.13	0.070	0.084	
L4	0.76	1.27	0.030	0.050	2
ØР	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° t	o 93°	90° to 93°		
		•	•		

#### Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimension: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline



### **Legal Disclaimer Notice**

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### **Material Category Policy**

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.

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